

# The Divisional Silicon Facility

- Purpose
- Current configuration
- Status

## Purpose

Provide appropriate space and basic technical facilities for

- bonding
  - assembly
  - testing
  - modifications
  - repair
  - R&D
- } of solid state detectors

## Basic idea

Group the assembly and test areas of LHC experiments around a common bonding lab under responsibility of division (EP/TA1-SD).

Bonding lab is open to all users (also non -LHC ones)!

## What are the requirements of the LHC experiments ?

- access to bonding lab: all 4 experiments. → presentation by Alan Honma
- assembly and test zones:
  - ALICE ca. 200 m<sup>2</sup>
  - ATLAS ca. 300 m<sup>2</sup>
  - CMS 1000m<sup>2</sup> (will prepare a zone under own responsibility, B186, 2nd floor)
  - LHCb ca. 50 m<sup>2</sup>

## Cleanroom classification

find compromise between cost, noise, discipline ↔ risk of detector or equipment failure due to dust.

Divide zone up into 3 sub-zones:

- bonding lab (SSDBL) <100.000 (zone A)
- clean zone ≈ 100.000 (zone B)
- less clean zone > 100.000 (zone C)

## Temperature control

$$\Delta L/L = \alpha \cdot \Delta T/T$$

$$\alpha = 10 - 20 \cdot 10^{-6} \text{ K}^{-1}$$

$$L = 10 \text{ cm} \rightarrow \Delta L = 1.5 \text{ } \mu\text{m/K}$$

Keep T at  $21 \pm 1^\circ\text{C}$ .

To be paid with air conditioning units.

## Humidity control

H too low → accumulation of electrostatic charges → damage of electronics

H too high → corrosion of surfaces, condensation at cold spots,

HV breakdown ( $V_{\text{bias}} = 400 \text{ V}$  over  $300 \mu\text{m} \approx E = 13.3 \text{ kV/cm}$ )

malfunctioning of electronic circuits and electrical machines.

Keep H at  $45 \pm 5\%$

To be paid with costly air treatment (cooling, heating, steam addition).

**Airborne Particulate  
Cleanliness Class  
Comparison**

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TA1 - SD

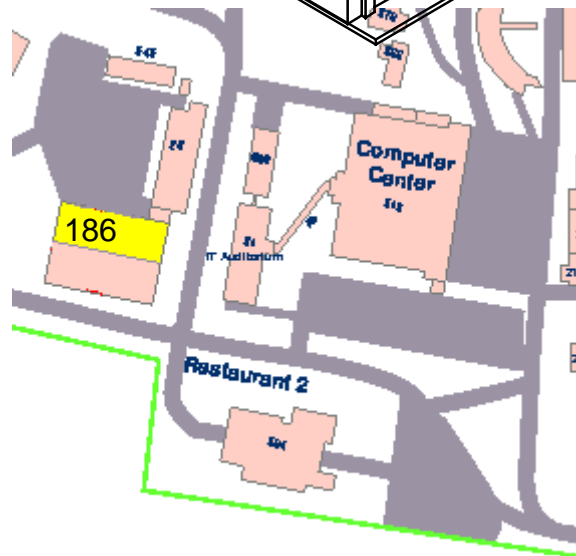
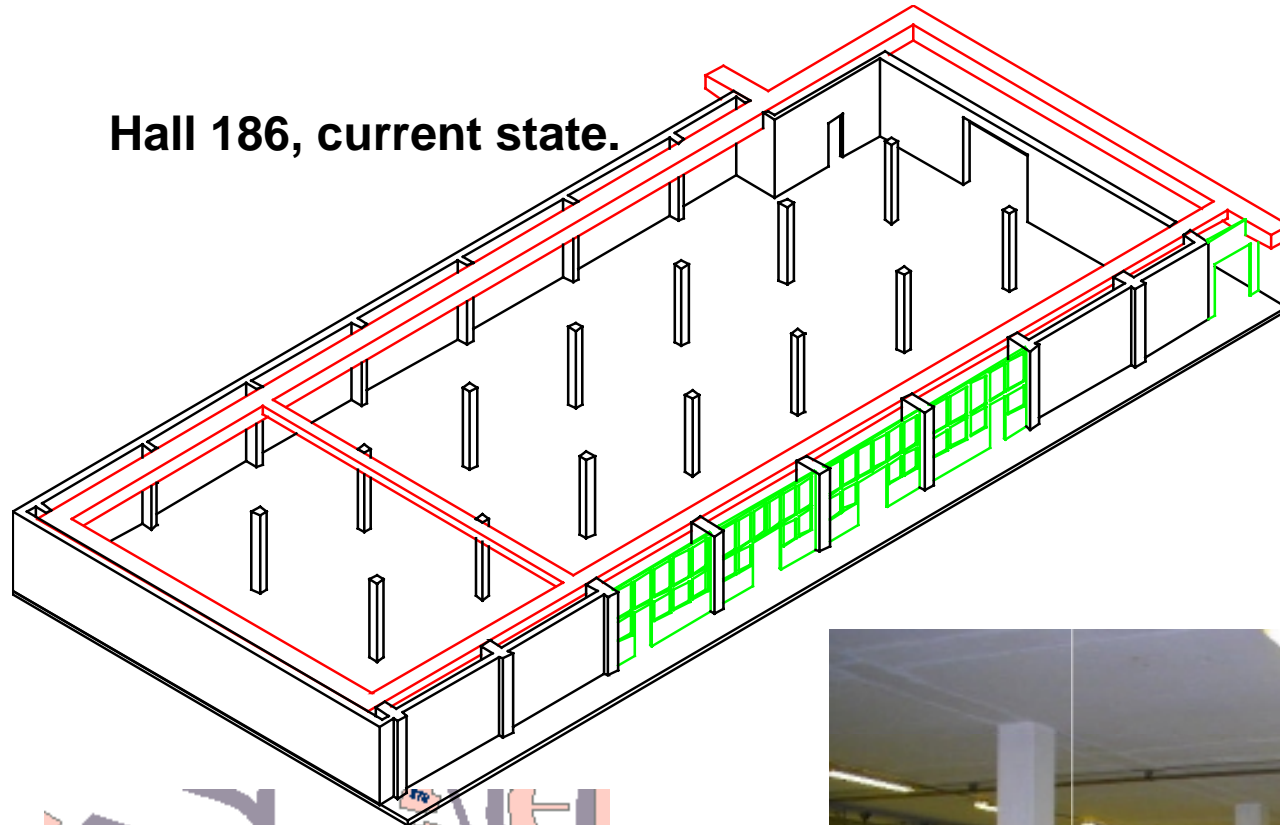
ISO 14644-1	FED STD 209E	
1		
2		
3	1	M1.5
4	10	M2.5
5	100	M3.5
6	1,000	M4.5
7	10,000	M5.5
8	100,000	M6.5
9		

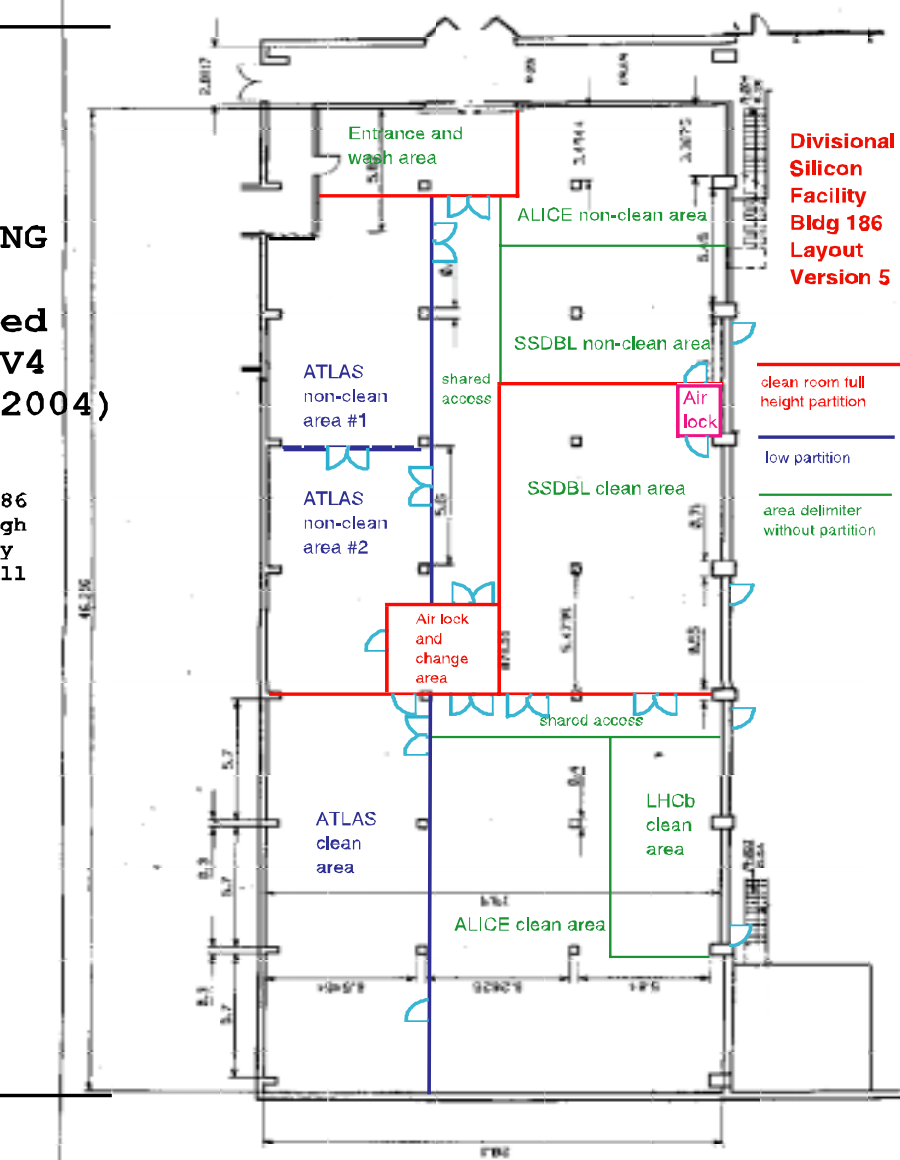
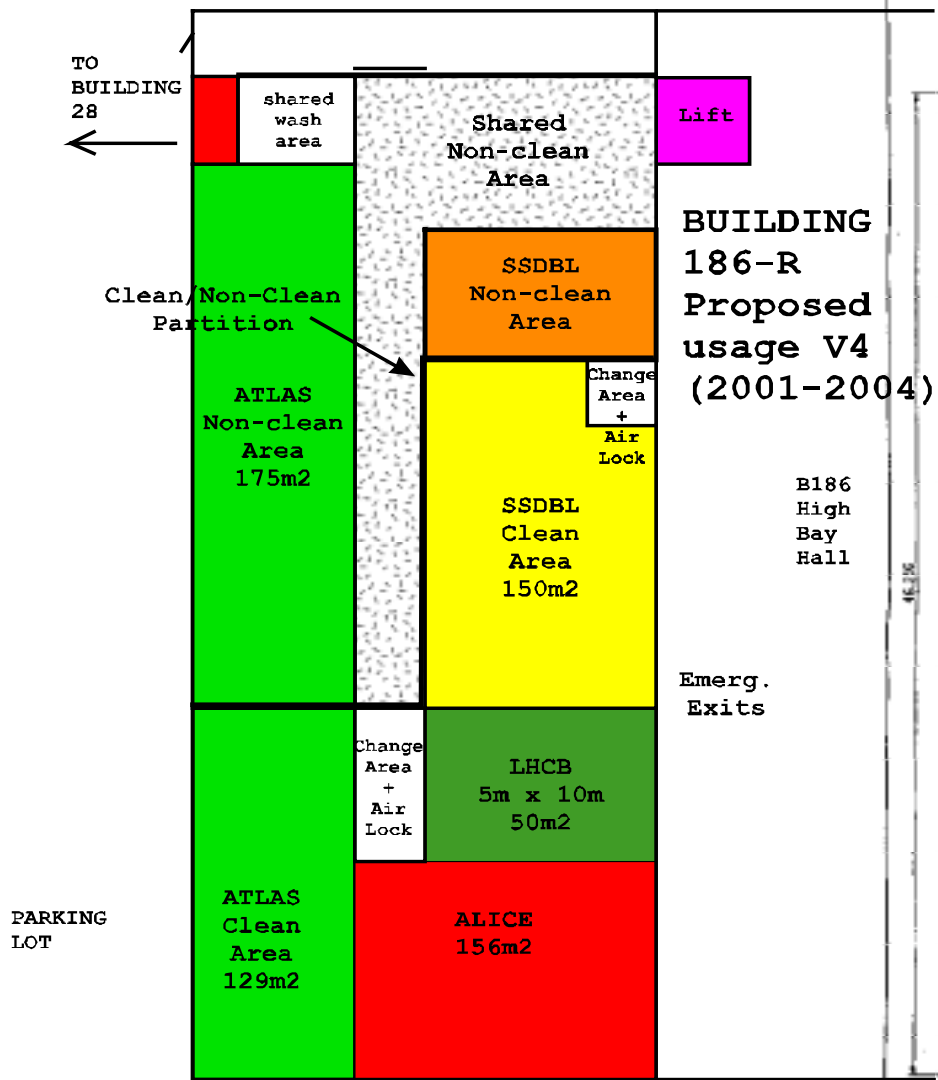
CLASS	Number of Particles per Cubic Meter by Micrometer Size					
	0.1 um	0.2 um	0.3 um	0.5 um	1 um	5 um
ISO 1	10	2				
ISO 2	100	24	10	4		
ISO 3	1,000	237	102	35	8	
ISO 4	10,000	2,370	1,020	352	83	
ISO 5	100,000	23,700	10,200	3,520	832	29
ISO 6	1,000,000	237,000	102,000	35,200	8,320	293
ISO 7				352,000	83,200	2,930
ISO 8				3,520,000	832,000	29,300
ISO 9				35,200,000	8,320,000	293,000

# Hall 186, current state.

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## Basic infrastructure

- New electricity network
- New lighting
- Structured telephone and ethernet
- Gas supplies (N<sub>2</sub>, Ar, CO<sub>2</sub>, comp. air)
- Cooling water, vacuum distribution lines
- Special floor (antistatic) and wall painting (washable)
- Air locks between non-clean and clean zones
- False ceiling in zones A and B.



## Current Status

- Performed a conceptual study of air treatment (together with company TEC)
- Technical discussions and price estimates for all subprojects

$\Sigma \approx 1$  MCHF

Discussions with division and LHC experiments on financing under way.

### If we reach an agreement on financing

- market survey
- call for tender
- start of work (air treatment installations) in September 2001

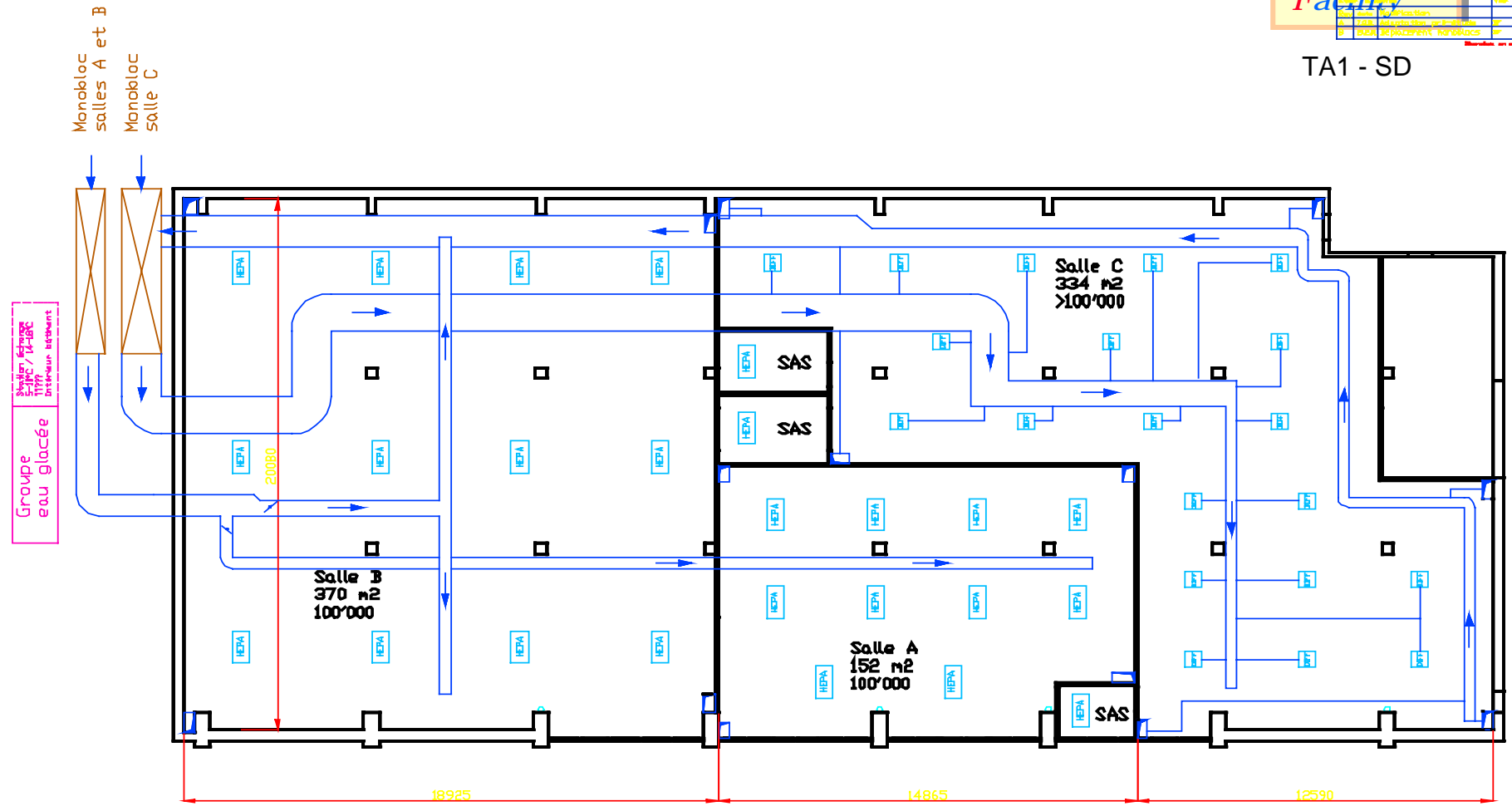
### If we don't reach an agreement

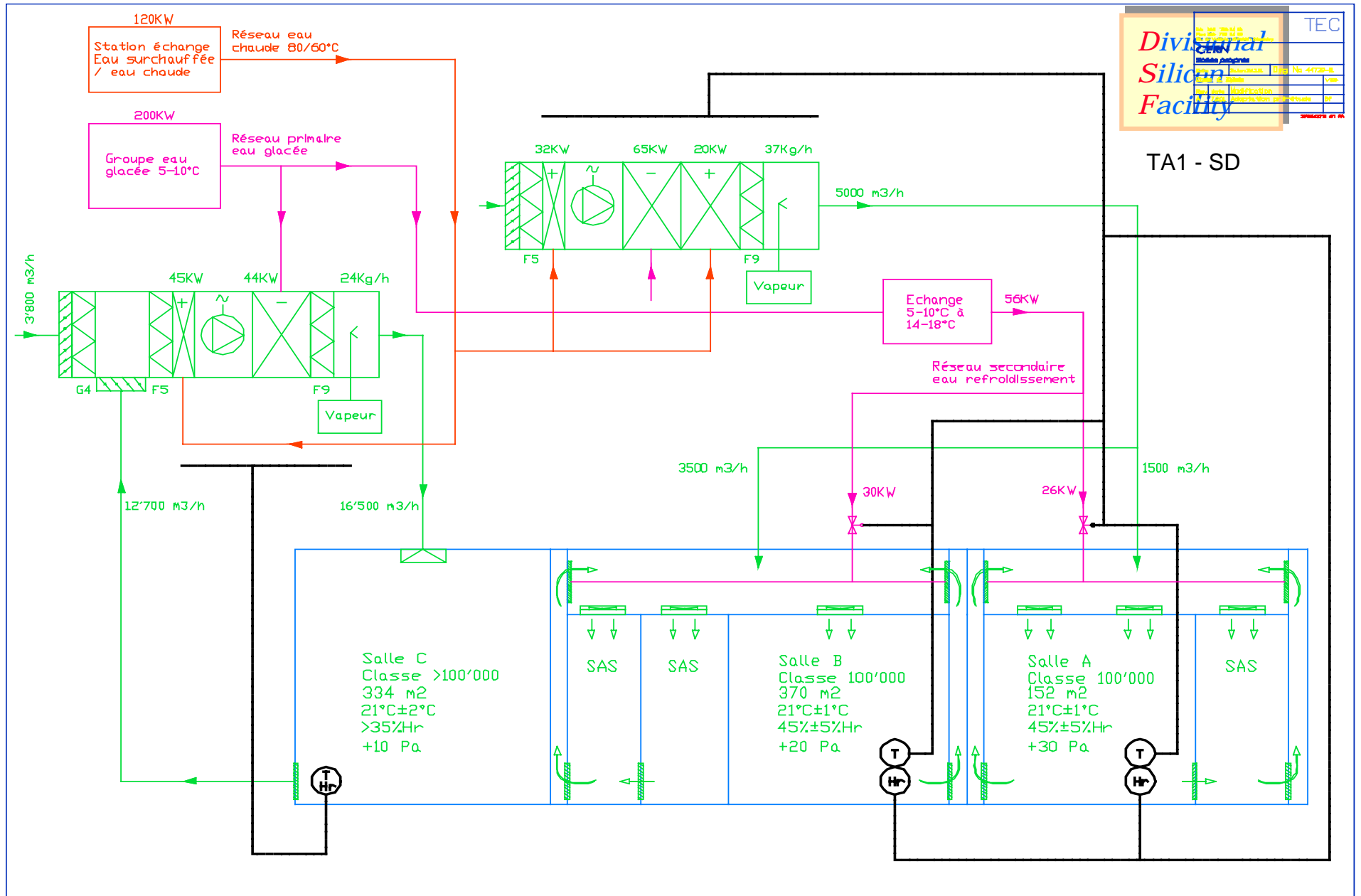
- reduce scope of project to SSDBL + hall space without air treatment
- possibly skip market survey
- call for tender
- start of work in July 2001

**Divisional** TEC  
**Silber**  
**Facility**

Proj. n°	14182
Client	TEC
Objet	TA1 - SD
Phase	SD
Échelle	1/1000
Établi par	C. Joram
Approuvé par	
Date	4 Avril 2001

TA1 - SD





**Division Silicon Facility**

TEC	
Projet	TA1-SD
Client	TA1-SD
Version	1.0
Date	04/04/2001
Échelle	
Intitulé	
Projet	
Client	
Version	
Date	
Échelle	
Intitulé	